CMOS High Voltage Logic – MM54C14J

Hex Schmitt Trigger Inverter in Ceramic Dual-In-Line Package (CDIP)

Rev 1.0
17/02/2023

Description

The MM54C14J Hex Schmitt Trigger is a monolithic complementary MOS (CMOS) integrated circuit constructed with N-channel and P-channel enhancement transistors. The positive and negative going threshold voltages, V_{T+} and V_{T-}, show low variation with respect to temperature (typ. 0.0005V/°C at V_{CC} = 10V), and hysteresis, $V_{T+} - V_{T-} \geq 0.2$ V_{CC} is guaranteed. All inputs are protected from damage due to static discharge by diode clamps to V_{CC} and GND.

Features:

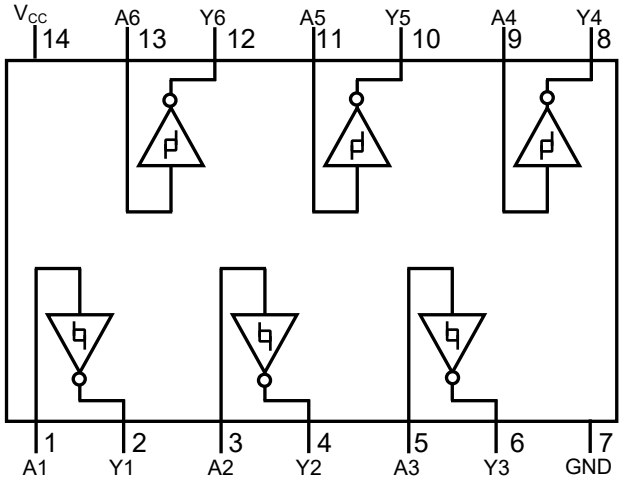
- Wide supply voltage range: 3V to 15V
- High noise immunity: 0.70 V_{CC} (typ.)
- Low power TTL compatibility:
  - 0.40 V_{CC} (typ.)
  - 0.20 V_{CC} (guaranteed)
- Hysteresis:
  - 0.40 V_{CC} (typ.)
  - 0.20 V_{CC} (guaranteed).

Ordering Information

The following part suffixes apply:

MM54C14J - 14 Lead Ceramic Dual-In-Line Package

Schematic & Connection Diagram



Function Table

INPUT A	OUTPUT Y
L	H
H	L

Absolute Maximum Ratings[1]

PARAMETER	SYMBOL	VALUE	UNIT
Voltage at any input pin	V_{IN}	-0.3 to V_{CC} + 0.3	V
Voltage at any output pin	V_{OUT}	-0.3 to V_{CC} + 0.3	V
Operating V_{CC} range	V_{CC}	3 to 15	V
Absolute maximum V_{CC}	$V_{CC(MAX)}$	18	V
Maximum Power Dissipation	P_D	700	mW
Operating Temperature Range	T_A	-55 to +125	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C
Lead Temperature (Soldering, 10 seconds)	T_L	260	°C

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

DC Electrical Characteristics T_A = -55 to +125°C unless otherwise stated

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CMOS TO CMOS						
Positive Going Threshold Voltage	V_{T+}	V_{CC} = 5V	3.0	3.6	4.3	V
		V_{CC} = 10V	6.0	6.8	8.6	V
		V_{CC} = 15V	9.0	10.0	12.9	V
Negative Going Threshold Voltage	V_{T-}	V_{CC} = 5V	0.7	1.4	2.0	V
		V_{CC} = 10V	1.4	3.2	4.0	V
		V_{CC} = 15V	2.1	5.0	6.0	V
Hysteresis	$V_{T+} - V_{T-}$	V_{CC} = 5V	1.0	2.2	3.6	V
		V_{CC} = 10V	2.0	3.6	7.2	V
		V_{CC} = 15V	3.0	5.0	10.8	V
Logical “1” Output Voltage	$V_{OUT(1)}$	V_{CC} = 5V, I_O = -10µA	4.5	-	-	V
		V_{CC} = 10V, I_O = -10µA	9.0	-	-	V
Logical “0” Output Voltage	$V_{OUT(0)}$	V_{CC} = 5V, I_O = 10µA	-	-	0.5	V
		V_{CC} = 10V, I_O = 10µA	-	-	1.0	V
Logical “1” Input Current	$I_{IN(1)}$	V_{CC} = 15V, V_{IN} = 15V	-	0.005	1.0	µA
Logical “0” Input Current	$I_{IN(0)}$	V_{CC} = 15V, V_{IN} = 0V	-1.0	-0.005	-	µA
Supply Current	I_{CC}	V_{CC} =15V,V_{IN}=0V/15V	-	0.05	15	µA
Supply Current[2]	I_{CC}	V_{CC} = 5V, V_{IN} = 2.5V	-	20	-	µA
		V_{CC} = 10V, V_{IN} = 5V	-	200	-	µA
		V_{CC} = 15V, V_{IN} = 7.5V	-	600	-	µA
CMOS/LPTTL INTERFACE						
Logical “1” Input Voltage	$V_{IN(1)}$	V_{CC} = 5V	4.3	-	-	V
Logical “0” Input Voltage	$V_{IN(0)}$	V_{CC} = 5V	-	-	0.7	V
Logical “1” Output Voltage	$V_{OUT(1)}$	V_{CC}= 4.5V,I_O= -360µA	2.4	-	-	V
Logical “0” Output Voltage	$V_{OUT(0)}$	V_{CC} =4.5V, I_O = 360µA	-	-	0.4	V
OUTPUT DRIVE CURRENT T_A = 25°C						
Output Source Current (P-Channel)	I_{SOURCE}	V_{CC} = 5V, V_{OUT} = 0V	-1.75	-3.3	-	mA
		V_{CC} = 10V, V_{OUT} = 0V	-8.0	-15	-	mA
Output Source Current (N-Channel)	I_{SINK}	V_{CC} = 5V, V_{OUT} = V_{CC}	1.75	3.6	-	mA
		V_{CC} = 10V, V_{OUT} = V_{CC}	8.0	16	-	mA
DYNAMIC ELECTRICAL CHARACTERISTICS[3] T_A = 25°C, C_L = 50pF unless otherwise stated						
Propagation Delay from Input to Output	t_{PD0}, t_{PD1}	V_{CC} = 5V	-	220	400	ns
		V_{CC} = 10V	-	80	200	ns
Input Capacitance	C_{IN}	Any Input	-	5.0	-	pF
Power Dissipation Capacitance[4]	C_{PD}	Per Gate	-	20	-	pF

2. Only one of the six inputs is at ½ V_{CC}; the others are either at V_{CC} or GND. **3.** Not production tested in die form, characterized by chip design.
4. Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

Typical Characteristics

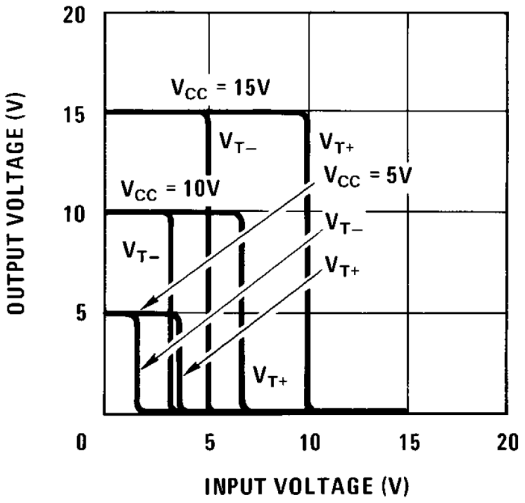


Figure 1 – Transfer Characteristics

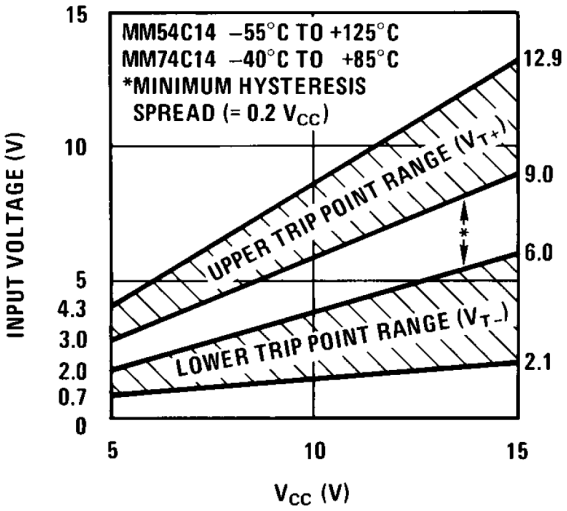


Figure 2 – Guaranteed Trip Point Range

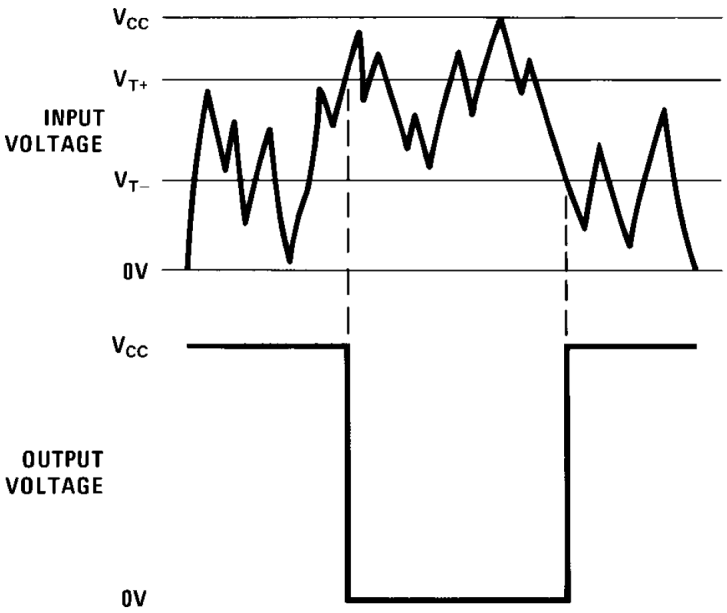


Figure 3 – Waveform

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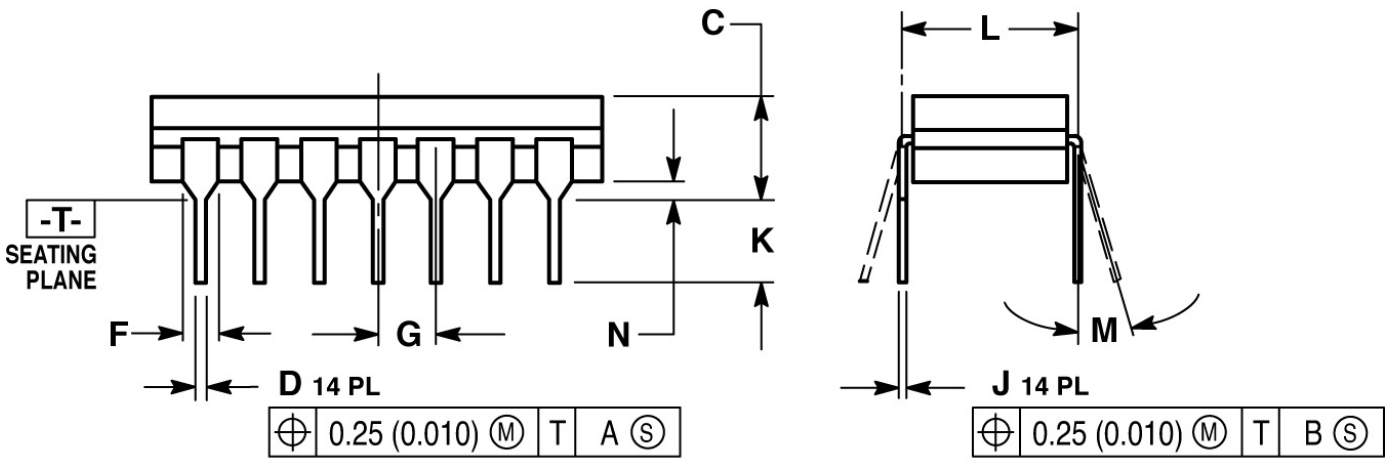
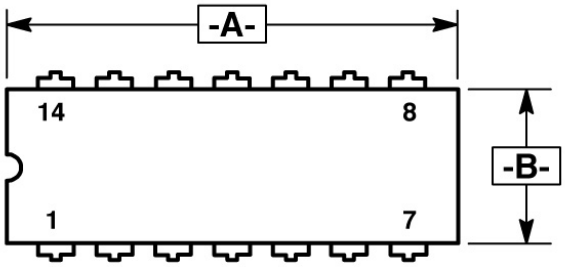
14 Lead Ceramic DIP - Package Dimensions and Footprint





DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.94
B	0.245	0.280	6.23	7.11
C	0.155	0.200	3.94	5.08
D	0.015	0.020	0.39	0.50
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01